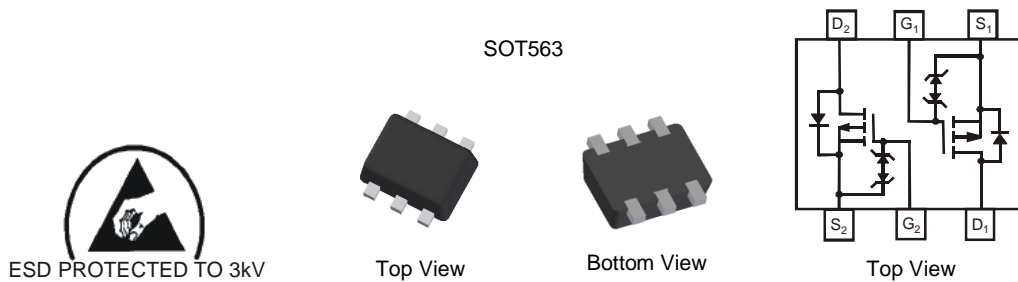


## Features

- Dual P-Channel MOSFET
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package
- **ESD Protected Up To 3kV**
- **Lead Free By Design/RoHS Compliant (Note 1)**
- **Halogen and Antimony Free "Green" Device (Note 2)**
- **Qualified to AEC-Q101 Standards for High Reliability**

## Mechanical Data

- Case: SOT563
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Terminals: Finish - Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.006 grams (approximate)

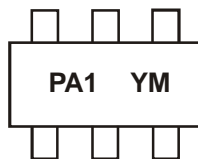


## Ordering Information (Note 3)

Part Number	Case	Packaging
DMG1023UV-7	SOT563	3,000 / Tape & Reel
DMG1023UV-13	SOT563	10,000 / Tape & Reel

- Notes:
1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. No purposely added lead. Halogen and Antimony free.
  2. Diodes Inc.'s "Green" Policy can be found on our website at <http://www.diodes.com>
  3. For packaging details, go to our website at <http://www.diodes.com>.

## Marking Information



PA1 = Product Type Marking Code  
 YM = Date Code Marking  
 Y = Year (ex: W = 2009)  
 M = Month (ex: 9 = September)

### Date Code Key

Year	2008	2009	2010	2011	2012	2013	2014	2015	2016	2017
Code	V	W	X	Y	Z	A	B	C	D	E

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

**Maximum Ratings** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V <sub>DSS</sub>	-20	V
Gate-Source Voltage			V <sub>GSS</sub>	±6	V
Continuous Drain Current (Note 4) V <sub>GS</sub> = -4.5V	Steady State	T <sub>A</sub> = 25°C	I <sub>D</sub>	-1.03	A
		T <sub>A</sub> = 85°C		-0.68	
Pulsed Drain Current (Note 5)			I <sub>DM</sub>	-3	A

**Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 4)	P <sub>D</sub>	530	mW
Thermal Resistance, Junction to Ambient @T <sub>A</sub> = 25°C (Note 4)	R <sub>θJA</sub>	235	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

**Electrical Characteristics** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition	
<b>OFF CHARACTERISTICS (Note 6)</b>							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-20	-	-	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = -250μA	
Zero Gate Voltage Drain Current T <sub>J</sub> = 25°C	I <sub>DSS</sub>	-	-	-100	nA	V <sub>DS</sub> = -20V, V <sub>GS</sub> = 0V	
Gate-Source Leakage	I <sub>GSS</sub>	-	-	±2.0	μA	V <sub>GS</sub> = ±4.5V, V <sub>DS</sub> = 0V	
<b>ON CHARACTERISTICS (Note 6)</b>							
Gate Threshold Voltage	V <sub>GS(th)</sub>	-0.5	-	-1.0	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250μA	
Static Drain-Source On-Resistance	R <sub>DS(on)</sub>	-	0.5	0.75	Ω	V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -430mA	
			0.7	1.05			V <sub>GS</sub> = -2.5V, I <sub>D</sub> = -300mA
			1.0	1.5			V <sub>GS</sub> = -1.8V, I <sub>D</sub> = -150mA
			-	20			V <sub>GS</sub> = -1.7V, I <sub>D</sub> = -100mA
			-	25			V <sub>GS</sub> = -1.5V, I <sub>D</sub> = -100mA
Forward Transfer Admittance	Y <sub>fs</sub>	-	0.9	-	S	V <sub>DS</sub> = -10V, I <sub>D</sub> = -250mA	
Diode Forward Voltage	V <sub>SD</sub>	-	-0.8	-1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = -150mA	
<b>DYNAMIC CHARACTERISTICS (Note 7)</b>							
Input Capacitance	C <sub>iSS</sub>	-	59.76	-	pF	V <sub>DS</sub> = -16V, V <sub>GS</sub> = 0V, f = 1.0MHz	
Output Capacitance	C <sub>oss</sub>	-	12.07	-	pF		
Reverse Transfer Capacitance	C <sub>rSS</sub>	-	6.36	-	pF		
Total Gate Charge	Q <sub>g</sub>	-	622.4	-	pC	V <sub>GS</sub> = -4.5V, V <sub>DS</sub> = -10V, I <sub>D</sub> = -250mA	
Gate-Source Charge	Q <sub>gs</sub>	-	100.3	-	pC		
Gate-Drain Charge	Q <sub>gd</sub>	-	132.2	-	pC		
Turn-On Delay Time	t <sub>D(on)</sub>	-	5.1	-	ns	V <sub>DD</sub> = -10V, V <sub>GS</sub> = -4.5V, R <sub>L</sub> = 47Ω, R <sub>G</sub> = 10Ω, I <sub>D</sub> = -200mA	
Turn-On Rise Time	t <sub>r</sub>	-	8.1	-	ns		
Turn-Off Delay Time	t <sub>D(off)</sub>	-	28.4	-	ns		
Turn-Off Fall Time	t <sub>f</sub>	-	20.7	-	ns		

- Notes:
- Device mounted on FR-4 PCB, with minimum recommended pad layout.
  - Repetitive rating, pulse width limited by junction temperature.
  - Short duration pulse test used to minimize self-heating effect.
  - Guaranteed by design. Not subject to production testing.

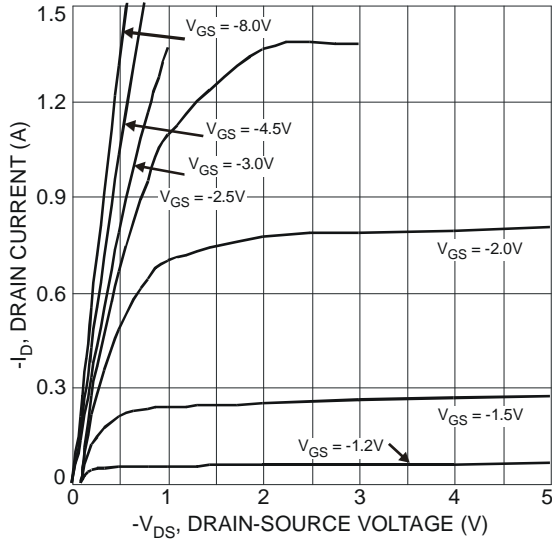


Fig. 1 Typical Output Characteristic

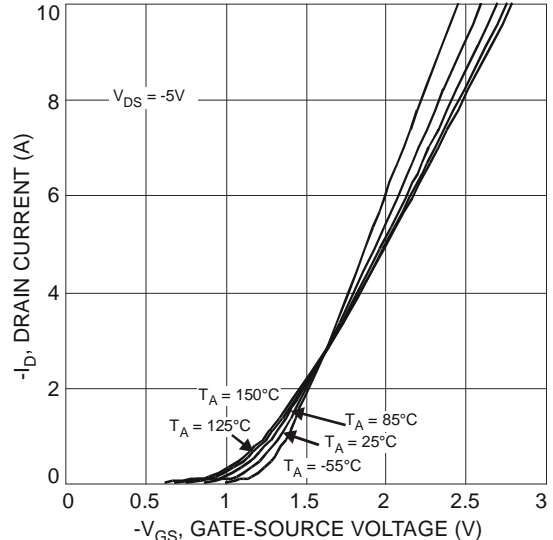


Fig. 2 Typical Transfer Characteristic

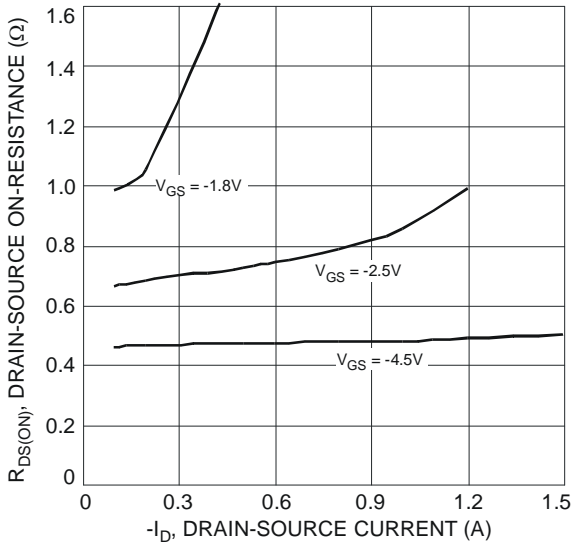


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

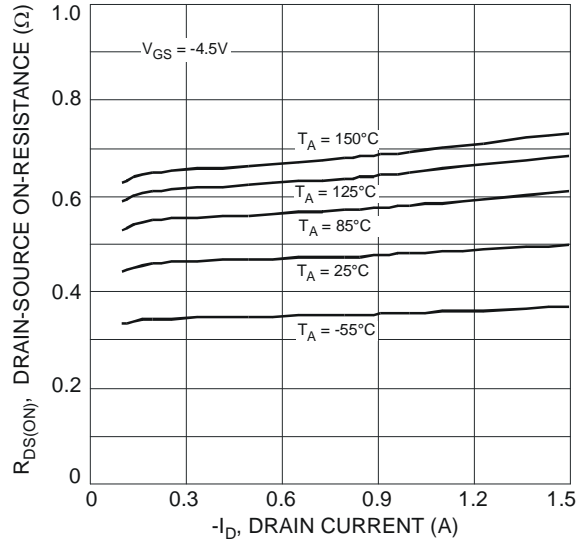


Fig. 4 Typical On-Resistance vs. Drain Current and Temperature

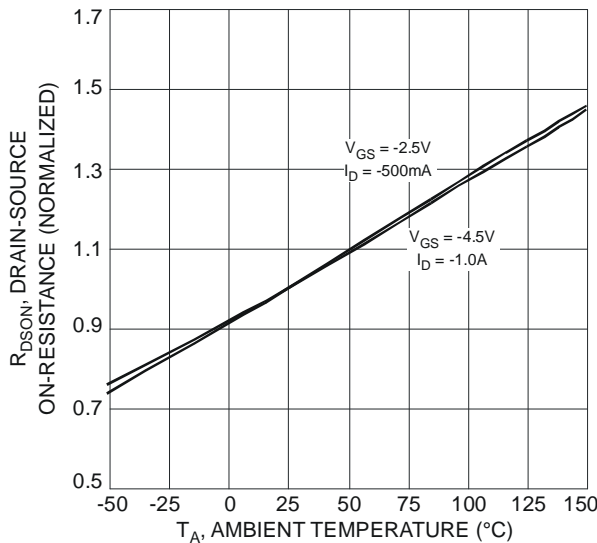


Fig. 5 On-Resistance Variation with Temperature

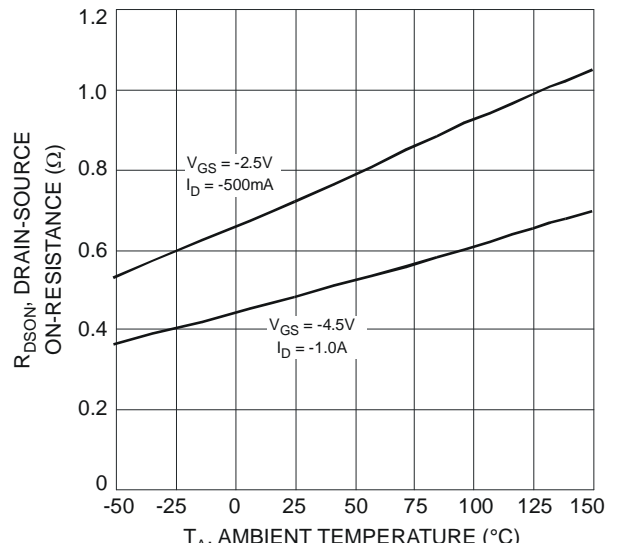


Fig. 6 On-Resistance Variation with Temperature

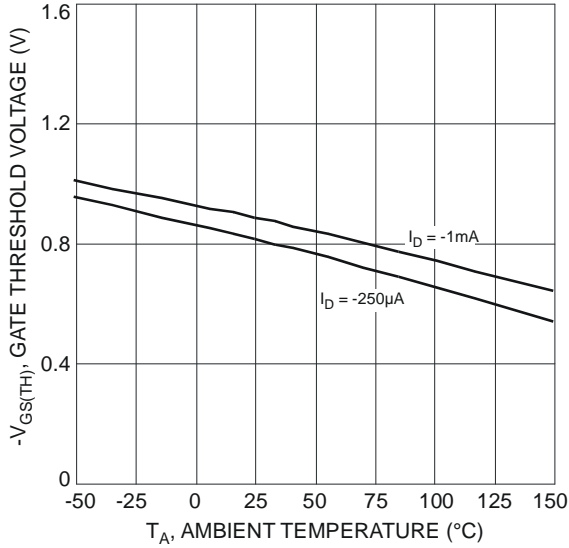


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

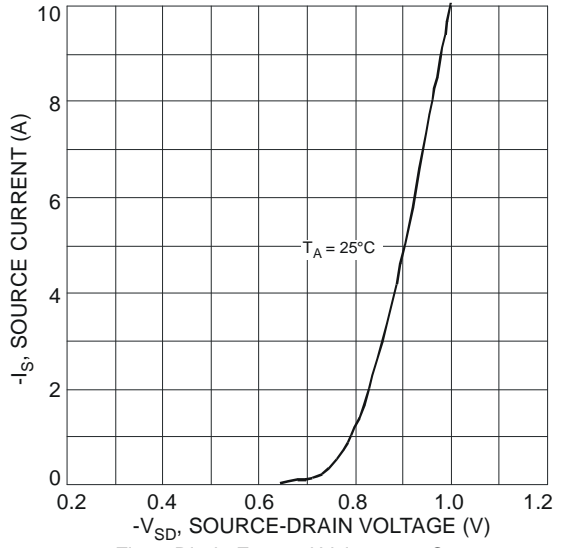


Fig. 8 Diode Forward Voltage vs. Current

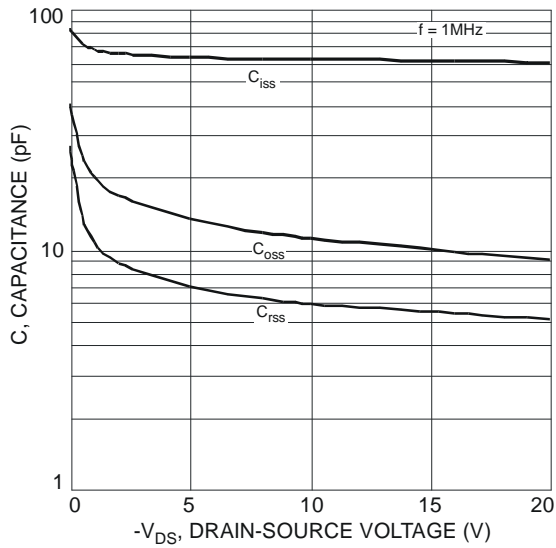


Fig. 9 Typical Total Capacitance

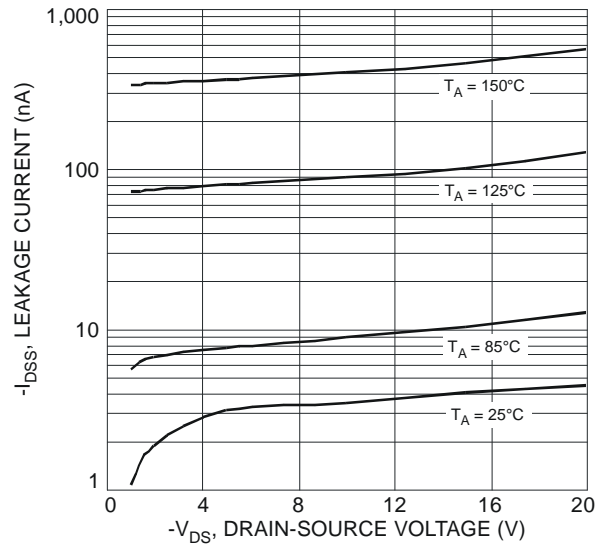


Fig. 10 Typical Leakage Current vs. Drain-Source Voltage

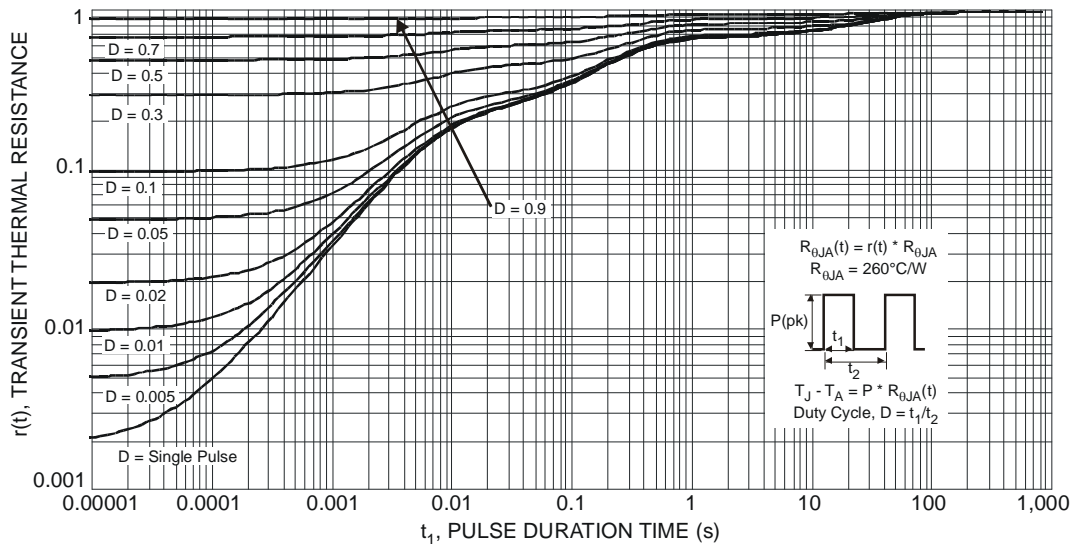
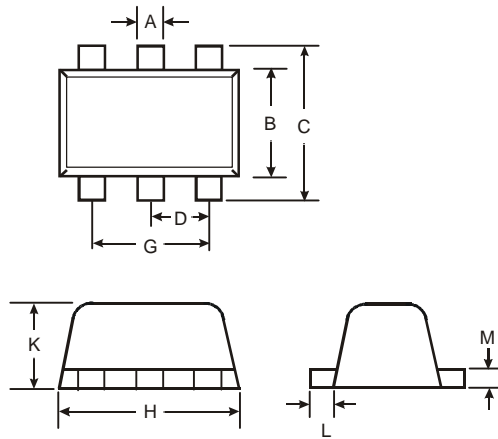


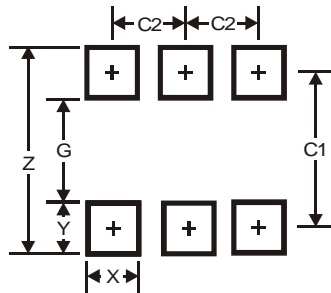
Fig. 11 Transient Thermal Response

**Package Outline Dimensions**



SOT563			
Dim	Min	Max	Typ
A	0.15	0.30	0.20
B	1.10	1.25	1.20
C	1.55	1.70	1.60
D	-	-	0.50
G	0.90	1.10	1.00
H	1.50	1.70	1.60
K	0.55	0.60	0.60
L	0.10	0.30	0.20
M	0.10	0.18	0.11
All Dimensions in mm			

**Suggested Pad Layout**



Dimensions	Value (in mm)
Z	2.2
G	1.2
X	0.375
Y	0.5
C1	1.7
C2	0.5

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